L	Hits	Search Text	DB	Time stamp
Number	7.5.			
_	1454		USPAT;	2004/07/08
		transistor fet mosfet) with (polysilicon	US-PGPUB	13:49
		poly polysi) with (oxidation oxidized oxidizing oxidate oxidating oxidize))	1	[
_	1533	(nmos pmos cmos nfet pfet) and ((gate	USPAT;	2004/07/07
	1333	transistor fet mosfet) with (polysilicon	US-PGPUB	11:11
		poly polysi) with (oxidation oxidized	OS IGIOD	
		oxidizing oxidate oxidating oxidize))		
_	3	(nmos pmos cmos nfet pfet) and ((gate	USPAT;	2004/07/08
		transistor fet mosfet) with (polysilicon	US-PGPUB	13:49
	:	poly polysi) with (oxidation oxidized		
		oxidizing oxidate oxidating oxidize) with	ŀ	
		stress\$)		
-	41	'	USPAT;	2004/07/08
		transistor fet mosfet) same ((polysilicon	US-PGPUB	13:51
		poly polysi) with (oxidation oxidized		
		oxidizing oxidate oxidating oxidize))		
_ •	2	same stress\$) 10/134201	IIGDAM.	2004/07/07
_	2	10/134201	USPAT;	2004/07/07
_	1	10/249228	US-PGPUB USPAT;	17:26
		10/11/20	US-PGPUB	17:33
_	3	10/134436	USPAT;	2004/07/07
]	20, 201100	US-PGPUB	18:36
_	67	("6228694" "6406973" "6281532" "5683934" "	6969A31" "53	120040445/1017/40875.3076" 11009
			US-PGPUB	18:58
-	0	2002/0090791	USPAT;	2004/07/07
			US-PGPUB	18:58
-	0	2002/0090791	USPAT;	2004/07/07
			US-PGPUB	18:58
_	1	"20020090791"	USPAT;	2004/07/07
		#20020074F00#	US-PGPUB	18:58
_	1	"20020074598"	USPAT;	2004/07/07
_	1	"20030040158"	US-PGPUB	18:59
	1	20030040138	USPAT; US-PGPUB	2004/07/07
_	1	"20020086472"	USPAT;	18:59 2004/07/07
	1	20020000172	US-PGPUB	19:00
-	71	(("6228694" "6406973" "6281532" "5683934"		
		or "20020090791" or "20020074598" or	US-PGPUB	13:46
-	23	"20030040158" or "20020086472"	USPAT;	2004/07/07
		((("6228694" "6406973" "6281532" "5683934"	U638699B" "	51391.004146" "4853076" "0
		or "20020090791" or "20020074598" or		
-	23	"20030040158" or "20020086472")	USPAT;	2004/07/07
		4nd"(6228d8t1on6696673td"628d532ng"568d88t"	"Beereru	51391.004146" "4853076 " "0
_	90	oxida000000000000000000000000000000000000		0004/07/55
•	28	"20030040158" or "20020086472") and	USPAT;	2004/07/07
		((여%6236694"여%64069335%142216325%18468934" oxid200260927812eprs#2002624598" or	 "¶ฤศฎฅ६वा	1,1973/14 1,148230
_	17	(20030040158" or "20020086472") and	USPAT;	2004/07/07
	• • •	(tenerale 604mprese 6923" "6281532" "5683934"	USEAL,	2004/07/07 5739-00546" "4853076" "0
		or "20020090791" or "20020074598" or	1 2025GB0D	0.1.0.1.0.1.0.1.0.1.0.1.0.1.0.1.0.1.0.1
		"20030040158" or "20020086472") and		
		((oxidation oxidized oxidizing oxidate		
-	6	<pre></pre>	USPAT;	2004/07/07
İ		((("6228694" "6406973" "6281532" "5683934"		51391.004546" "4853076" "0
		or "20020090791" or "20020074598" or	- '	, , , , , , , , , , , , , , , , , , , ,
		"20030040158" or "20020086472") and		
ļ		(temsdaeionmpxedszwd) pxidizing oxidate		
İ		oxidating oxidize) same stress\$)) not ((
l		((("6228694" "6406973" "6281532" "5683934"		5310446" "4853076 " "0
-	11	or "20020090791" or "20020074598" or	USPAT;	2004/07/07
ł		"(200800869887"64080002008881332"4Md683934"	្រាធខាងខេត្តពារា	51391.004616" "4853076 " "0
		otoX2dataaaadaaadaaadaaadaadaadaadaadaadaadaa		
		820da60161521doze 2281200864235\$) andnd (1 " 62 6002 " . "	F3104468184050555
		(tens218686mpr6485923) n6281332" "5683934" or("80086990796406973200808783987"5683934"	"6369031" "	5310446" "4853076" "0
		820020020099796F 820020086672598ändr	TE600C0	2210440 48230./61. 00
		(200300404567501 02002002047535011d1 (20030040455611d1) and		

			·	
-	71	(("6228694" "6406973" "6281532" "5683934"		I The state of the
_	6	or "20020090791" or "20020074598" or "2400800869887"640890024008881232" "5683934"	US-PGPUB IIII G B K R 9 3 1 " I "	13:46 5200004/057//024853076/* "0090
-	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	or "20020090791" or "20020074598" or	US-PGPUB	13:46
-	4	(20630880158""5683909200888924001and	USPAT	2004/07/08
		d6916098").PN.		13:48
-	1	6362082.URPN.	USPAT	2004/07/08
	2	6281532.URPN.	HCDAM	13:48
-	2	6281332.URPN.	USPAT	2004/07/08
_	3	(nmos pmos cmos nfet cmosfet pfet nmosfet	USPAT;	2004/07/08
}		pmosfet) and ((gate transistor fet	US-PGPUB	13:50
	•	mosfet) with (polysilicon poly polysi)		
		with (oxidation oxidized oxidizing		
_	41	oxidate oxidating oxidize) with stress\$) (nmos pmos cmos nfet pfet cmosfet nmosfet	USPAT;	2004/07/08
	**	pmosfet) and ((gate transistor fet	US-PGPUB	13:50
		mosfet) same ((polysilicon poly polysi)		
		with (oxidation oxidized oxidizing		ĺ
		oxidate oxidating oxidize)) same stress\$)		
-	8	(((nmos nfet nmosfet) with tensile) same (oxidation oxidized oxidizing oxidate	USPAT; US-PGPUB	2004/07/08
		oxidation oxidized oxidizing oxidate oxidating oxidize)) and (cmosfet cmos	OS-FGFUD	13.37
		pfet pmos pmosfet)		
-	37	,, ,, ,,	USPAT;	2004/07/08
		oxidized oxidizing oxidate oxidating	US-PGPUB	13:58
_	35	oxidize) with (polysilicon poly polysi) ((nmos nfet nmosfet) with (oxidation	USPAT;	2004/07/08
	33	oxidized oxidizing oxidate oxidating	US-PGPUB	15:02
		oxidize) with (polysilicon poly polysi))	0.5 1 0.1 0.5	10.02
	_	and (pmos pmosfet pfet cmos cmosfet)		
_	0	((oxidiz\$ near2 (nfet nmos nmosfet)) with tensile)	USPAT;	2004/07/08
_	0	((oxidat\$ near2 (nfet nmos nmosfet)) with	US-PGPUB USPAT;	15:03 2004/07/08
	Ĭ	tensile)	US-PGPUB	15:03
-	1	' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	USPAT;	2004/07/08
		tensile)	US-PGPUB	15:03
_	0	((oxidiz\$ with (nfet nmos nmosfet)) with tensile)	USPAT; US-PGPUB	2004/07/08 15:05
_	2	((oxidat\$ with (nfet nmos nmosfet)) with	USPAT;	2004/07/08
		tensile)	US-PGPUB	15:04
-	0	((oxidat\$ with (nfet nmos nmosfet)) with	EPO; JPO;	2004/07/08
		tensile)	DERWENT;	15:04
-	o	((oxidiz\$ with (nfet nmos nmosfet)) with	IBM_TDB EPO; JPO;	2004/07/08
		tensile)	DERWENT;	15:05
		(4420/400)	IBM_TDB	
-	1713	((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or	USPAT;	2004/07/08
		(438/233)).CCLS.	US-PGPUB	15:08
-	346	(438/279).CCLS.	USPAT;	2004/07/08
	:		US-PGPUB	15:08
-	2024	(((438/199) or (438/218) or (438/229) or	USPAT;	2004/07/08
]		(438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)	US-PGPUB	15:09
-	1352	((((438/199) or (438/218) or (438/229) or	USPAT;	2004/07/08
		(438/230) or (438/231) or (438/232) or	US-PGPUB	15:10
		(438/233)).CCLS.) or ((438/279).CCLS.))		
_	159	and (CMOS CMOSFET complementary) (((((438/199) or (438/218) or (438/229)	USPAT;	2004/07/08
ļ		or (438/230) or (438/231) or (438/232) or	US-PGPUB	15:16
]		(438/233)).CCLS.) or ((438/279).CCLS.))	·	
		and (CMOS CMOSFET complementary)) and		
_	159	(stress\$ tensile compressive) ((((((438/199) or (438/218) or (438/229)	USPAT;	2004/07/08
	159	or (438/230) or (438/231) or (438/232) or	US-PGPUB	2004/07/08 15:14
		(438/233)).CCLS.) or ((438/279).CCLS.))	22 20200	
<u> </u>		and (CMOS CMOSFET complementary)) and		
		(stress\$ tensile compressive)) not (@ad>20030923 or @rlad>20030923)		
		(GAG/20030923 OF GETAG/20030923)		

-	1243	(((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or	USPAT; US-PGPUB	2004/07/08 15:16
		(438/233)).CCLS.) or ((438/279).CCLS.))		
1		and (CMOS CMOSFET complementary)) and		
		((oxidiz\$ oxidat\$ oxide) with (gate transistor fet mosfet nfet nmosfet))		
-	572		USPAT;	2004/07/08
		or (438/230) or (438/231) or (438/232) or	US-PGPUB	15:17
		(438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and		
		((oxidiz\$ oxidat\$) with (gate transistor		
		fet mosfet nfet nmosfet))		
-	80	(((((((((((((((((((((((((((((((((((((USPAT;	2004/07/08
		or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.))	US-PGPUB	15:17
		and (CMOS CMOSFET complementary)) and		
		(stress\$ tensile compressive)) not		
		(@ad>20030923 or @rlad>20030923)) and		
		((((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or		
		(438/233)).CCLS.) or ((438/279).CCLS.))		
		and (CMOS CMOSFET complementary)) and		
		((oxidiz\$ oxidat\$) with (gate transistor		
-	78	fet mosfet nfet nmosfet))) ((((((((438/199) or (438/218) or	USPAT;	2004/07/08
		(438/229) or (438/230) or (438/231) or	US-PGPUB	15:46
		(438/232) or (438/233)).CCLS.) or		
		((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and (stress\$ tensile		}
		compressive)) not (@ad>20030923 or		
		@rlad>20030923)) and (((((438/199) or		
		(438/218) or (438/229) or (438/230) or		
		(438/231) or (438/232) or (438/233)).CCLS.))		
		and (CMOS CMOSFET complementary)) and		
		((oxidiz\$ oxidat\$) with (gate transistor		
		fet mosfet nfet nmosfet)))) not ((nmos		İ
}		pmos cmos nfet pfet cmosfet nmosfet pmosfet) and ((gate transistor fet		
•		mosfet) same ((polysilicon poly polysi)		
		with (oxidation oxidized oxidizing		
		oxidate oxidating oxidize)) same stress\$))		
_	76828	cmos Cmosfet	USPAT;	2004/07/08
			US-PGPUB	15:47
-	2407	(cmos Cmosfet) and (mask with (nitride	USPAT;	2004/07/08
_	182	and (PR photoresist))) (cmos Cmosfet) and (mask with (nitride	US-PGPUB USPAT;	15:56
		near2 (PR photoresist)))	US-PGPUB	2004/07/08 15:56
-	91	(cmos Cmosfet) and (mask near2 (nitride	USPAT;	2004/07/08
_	0	<pre>near2 (PR photoresist))) (cmos Cmosfet) and (mask near2 (nitride</pre>	US-PGPUB	15:56
		near2 (PR photoresist)) with "or")	USPAT; US-PGPUB	2004/07/08
-	0	(cmos Cmosfet) and (mask with (nitride	USPAT;	2004/07/08
		<pre>near2 (PR photoresist))with "or")</pre>	US-PGPUB	15:56
-	0	<pre>(cmos Cmosfet) and (mask with (nitride and (PR photoresist))with "or")</pre>	USPAT;	2004/07/08
_	0	(cmos Cmosfet) and ((silicide or	US-PGPUB USPAT;	16:06 2004/07/08
		salicide) with (remove with unreacted)	US-PGPUB	16:07
_		with (nfet nmos nmosfet))	II.a.n.T.	0004/07/05
	0	(cmos Cmosfet) and ((silicide or salicide) with (remove with unreacted)	USPAT; US-PGPUB	2004/07/08
		same (nfet nmos nmosfet))	US FGFUD	10.07
-	146	(cmos Cmosfet) and ((silicide or	USPAT;	2004/07/08
_	6	salicide) with (remove with unreacted))	US-PGPUB	17:18
	"	(cmos Cmosfet) and ((silicide or salicide) with (remove) with (NFET nmos	USPAT; US-PGPUB	2004/07/08
		nmosfet))	OD IGEOD	17.10
-	5	(cmos Cmosfet) and ((silicide Cosi tisi	USPAT;	2004/07/08
		wsi mosi) with (remove) with (NFET nmos nmosfet))	US-PGPUB	17:10
				1

	0	1//	IICDAM.	1 2004 (07 (00
	0	((cmos Cmosfet) and ((silicide Cosi tisi wsi mosi) with (remove) with (NFET nmos	USPAT; US-PGPUB	2004/07/08
		nmosfet))) not ((cmos Cmosfet) and	US-PGPUB	17:10
		((silicide or salicide) with (remove)		
				-
	200	with (NFET nmos nmosfet)))		0004/07/00
-	226	(jennifer near2 kennedy).xa.	USPAT;	2004/07/08
		(//:	US-PGPUB	17:14
-	77	[, , ,	USPAT;	2004/07/08
	1.4	silicide	US-PGPUB	17:14
-	14	'',	USPAT;	2004/07/08
	ļ	((silicide salicide cosi wsi tisi) with	US-PGPUB	17:15
	595	remov\$)		0004/07/00
_	995	(cmos Cmosfet) and ((silicide or	USPAT;	2004/07/08
	440	salicide) with (remov\$ with unreacted))	US-PGPUB	17:18
-	449	(USPAT;	2004/07/08
		salicide) with (remov\$ with unreacted)))	US-PGPUB	17:18
	1	not ((cmos Cmosfet) and ((silicide or		
	21	salicide) with (remove with unreacted)))		2004/07/00
-	21		USPAT;	2004/07/08
		salicide) with (remov\$) with (NFET nmos nmosfet))	US-PGPUB	17:27
_	21	1	*******	2004/07/00
	21	cosi mosi tisi wsi) with (remov\$) with	USPAT; US-PGPUB	2004/07/08
		(NFET nmos nmosfet))	US-PGPUB	17:28
_	0		USPAT;	2004/07/08
	0	cosi mosi tisi wsi) with (remov\$ etching	US-PGPUB	17:28
		etched etch) with (NFET nmos nmosfet)	US-PGPUB	17:28
ļ		with top)		
_	126		USPAT;	2004/07/08
ļ	120	cosi mosi tisi wsi) with (remov\$ etching	US-PGPUB	17:29
ľ		etched etch) with (NFET nmos nmosfet gate	US-FGFUB	17.29
		transistor fet) with top)		
_	126		USPAT;	2004/07/08
ŀ	120	cosi mosi tisi wsi) with (remov\$ etching	US-PGPUB	17:30
ļ		etched etch) with (NFET nmos nmosfet gate	05-FGF0B	17.30
		transistor fet mosfet) with top)		
_	19	(cmos Cmosfet) and ((silicide or salicide	USPAT;	2004/07/08
		cosi mosi tisi wsi) with ((remov\$ etching	US-PGPUB	19:07
		etched etch) near2 top) with (NFET nmos	05 10105	13.07
		nmosfet gate transistor fet mosfet))		
_	19	"5828131"	USPAT;	2004/07/08
			US-PGPUB	19:08
-	1	("5828131").PN.	USPAT;	2004/07/08
			US-PGPUB	19:07
-	1	"20020031909"	USPAT;	2004/07/08
ļ			US-PGPUB	19:09
-	0	"200400087160"	USPAT;	2004/07/08
			US-PGPUB	19:09
-	1	"20040087160"	USPAT;	2004/07/08
			US-PGPUB	19:09